



SANYO Semiconductors DATA SHEET

N-Channel Silicon MOSFET

BFL4004 — General-Purpose Switching Device Applications

Features

- ON-resistance RDS(on)= 1.9Ω (typ.)
- Input capacitance Ciss=710pF (typ.)
- 10V drive

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		800	V
Gate-to-Source Voltage	V _{GSS}		±30	V
Drain Current (DC)	I _{Dc} *1	Limited only by maximum temperature Tch=150°C	6.5	А
	I _{Dpack} *2	Tc=25°C (SANYO's ideal heat dissipation condition)*3	4.3	А
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	13	А
Allowable Power Dissipation	D-		2.0	W
	PD	Tc=25°C (SANYO's ideal heat dissipation condition)*3	36	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C
Avalanche Energy (Single Pulse) *4	EAS		241	mJ
Avalanche Current *5	I _{AV}		6.5	Α

Note:*1 Shows chip capability

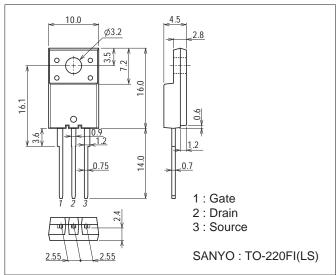
- *2 Package limited
- *3 SANYO's condition is radiation from backside.

The method is applying silicone grease to the backside of the device and attaching the device to water-cooled radiator made of aluminium.

- *4 V_{DD}=99V, L=10mH, I_AV=6.5A (Fig.1)
- *5 L≤10mH, single pulse

Package Dimensions

unit : mm (typ) 7509-002



Product & Package Information

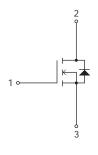
• Package : TO-220FI(LS)

JEITA, JEDEC : SC-67, SOT-186A, TO-220F
 Minimum Packing Quantity : 100 pcs./bag or 50pcs./magazine

Marking

FL4004 | LOT NO.

Electrical Connection





Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Uniii
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=10mA, VGS=0V	800			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =640V, V _{GS} =0V			1.0	mA
Gate-to-Source Leakage Current	IGSS	V _{GS} =±30V, V _{DS} =0V			±100	nA
Cutoff Voltage	VGS(off)	V _{DS} =10V, I _D =1mA	2.0		4.0	V
Forward Transfer Admittance	yfs	VDS=20V, ID=3.25A	1.7	3.4		S
Static Drain-to-Source On-State Resistance	R _{DS} (on)	I _D =3.25A, V _G S=10V		1.9	2.5	Ω
Input Capacitance	Ciss	V _{DS} =30V, f=1MHz		710		pF
Output Capacitance	Coss	V _{DS} =30V, f=1MHz		120		pF
Reverse Transfer Capacitance	Crss	V _{DS} =30V, f=1MHz		42		pF
Turn-ON Delay Time	t _d (on)	See Fig.2		17		ns
Rise Time	t _r	See Fig.2		44		ns
Turn-OFF Delay Time	t _d (off)	See Fig.2		130		ns
Fall Time	tf	See Fig.2		44		ns
Total Gate Charge	Qg	V _{DS} =200V, V _{GS} =10V, I _D =6.5A		36		nC
Gate-to-Source Charge	Qgs	V _{DS} =200V, V _{GS} =10V, I _D =6.5A		6.2		nC
Gate-to-Drain "Miller" Charge	Qgd	V _{DS} =200V, V _{GS} =10V, I _D =6.5A		18		nC
Diode Forward Voltage	VSD	IS=6.5A, VGS=0V		0.85	1.2	V
Reverse Recovery Time	t _{rr}	See Fig.3		780		ns
Reverse Recovery Charge	Q _{rr}	IS=6.5A, VGS=0V, di/dt=100A/μs		5400		nC

Fig.1 Avalanche Resistance Test Circuit

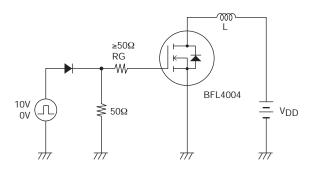


Fig.2 Switching Time Test Circuit

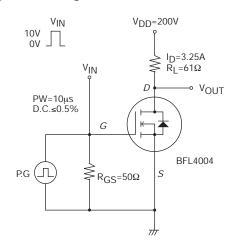
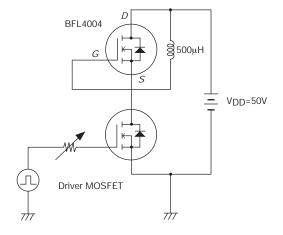
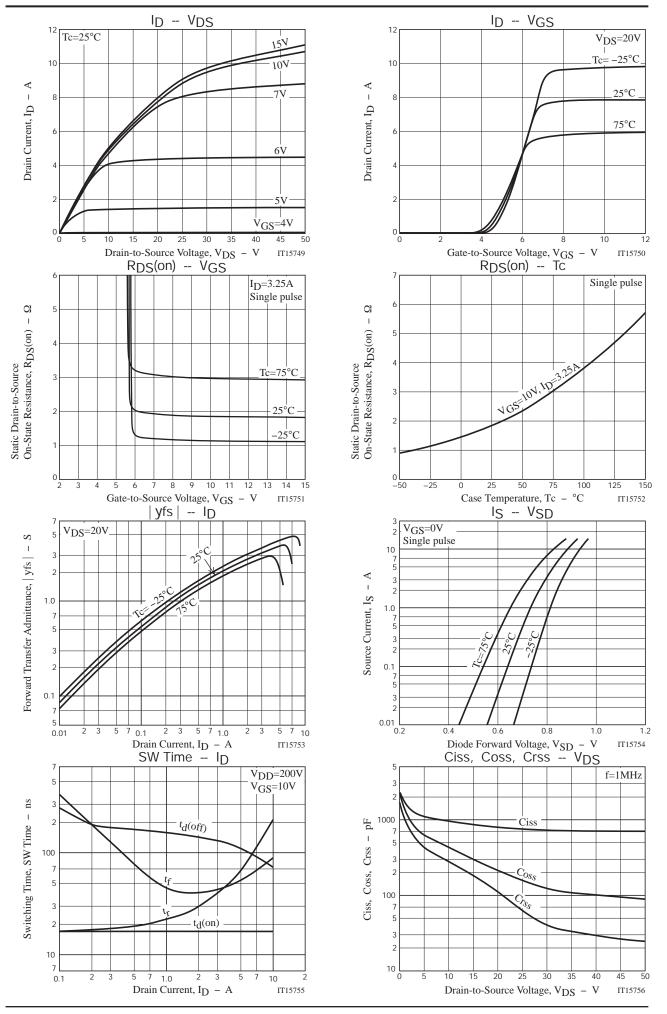
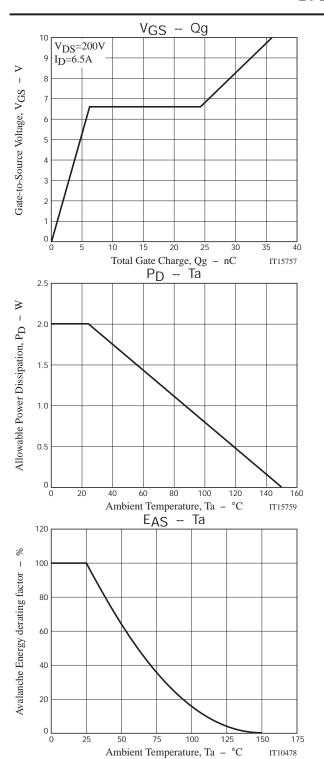


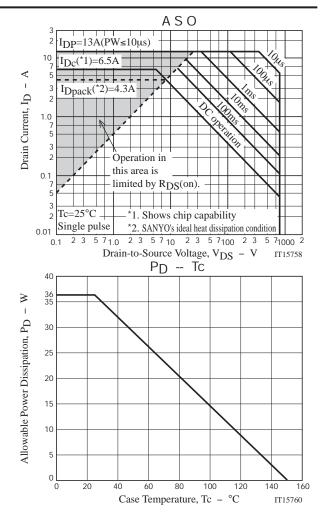
Fig.3 t_{rr} Reverse Recovery Time Test Circuit













Note on usage: Since the BFL4004 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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